

FMH11N90E

FUJI POWER MOSFET

Super FAP-E³ series

N-CHANNEL SILICON POWER MOSFET

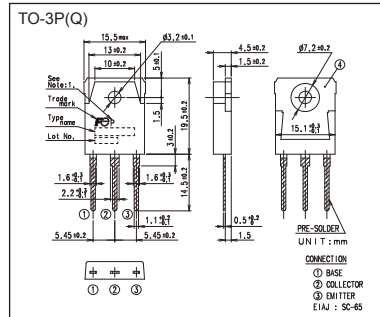
Features

- Maintains both low power loss and low noise
- Lower R_{DS(on)} characteristic
- More controllable switching dv/dt by gate resistance
- Smaller V_{GS} ringing waveform during switching
- Narrow band of the gate threshold voltage (4.0±0.5V)
- High avalanche durability

Applications

- Switching regulators
- UPS (Uninterruptible Power Supply)
- DC-DC converters

Outline Drawings [mm]



Equivalent circuit schematic



Maximum Ratings and Characteristics

Absolute Maximum Ratings at T_c=25°C (unless otherwise specified)

Description	Symbol	Characteristics	Unit	Remarks
Drain-Source Voltage	V _{DS}	900	V	
	V _{DSDX}	900	V	V _{GS} = -30V
Continuous Drain Current	I _D	±11	A	
Pulsed Drain Current	I _{DP}	±44	A	
Gate-Source Voltage	V _{GS}	±30	V	
Repetitive and Non-Repetitive Maximum Avalanche Current	I _{AR}	11	A	Note*1
Non-Repetitive Maximum Avalanche Energy	E _{AS}	811.9	mJ	Note*2
Repetitive Maximum Avalanche Energy	E _{AR}	28.5	mJ	Note*3
Peak Diode Recovery dV/dt	dV/dt	2.2	kV/μs	Note*4
Peak Diode Recovery -di/dt	-di/dt	100	A/μs	Note*5
Maximum Power Dissipation	P _D	2.5	W	T _a =25°C
		285		T _c =25°C
Operating and Storage Temperature range	T _{ch}	150	°C	
	T _{stg}	-55 to +150	°C	

Electrical Characteristics at T_c=25°C (unless otherwise specified)

Description	Symbol	Conditions	min.	typ.	max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	I _D =250μA, V _{GS} =0V	900	-	-	V
Gate Threshold Voltage	V _{GS(th)}	I _D =250μA, V _{DS} =V _{GS}	3.5	4.0	4.5	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =900V, V _{GS} =0V	-	-	25	μA
		V _{DS} =720V, V _{GS} =0V	-	-	250	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0V	-	10	100	nA
Drain-Source On-State Resistance	R _{DS(on)}	I _D =5.5A, V _{GS} =10V	-	0.83	1.0	Ω
Forward Transconductance	g _{fs}	I _D =5.5A, V _{DS} =25V	6.5	13	-	S
Input Capacitance	C _{iss}	V _{DS} =25V	-	2300	3450	pF
Output Capacitance	C _{oss}	V _{GS} =0V	-	200	300	
Reverse Transfer Capacitance	C _{rss}	f=1MHz	-	15	22.5	
Turn-On Time	td(on)	V _{CC} =600V	-	37	56	ns
	tr	V _{GS} =10V	-	32	48	
Turn-Off Time	td(off)	I _D =5.5A	-	124	186	
	tf	R _G =20Ω	-	34	51	
Total Gate Charge	Q _G	V _{CC} =450V	-	60	90	nC
Gate-Source Charge	Q _{GS}	I _D =11A	-	17	26	
Gate-Drain Charge	Q _{GD}	V _{GS} =10V	-	23	35	
Gate-Drain Crossover Charge	Q _{SW}		-	7	11	
Avalanche Capability	I _{AV}	L=4.92mH, T _{ch} =25°C	11	-	-	A
Diode Forward On-Voltage	V _{SD}	I _F =11A, V _{GS} =0V, T _{ch} =25°C	-	0.90	1.35	V
Reverse Recovery Time	t _{rr}	I _F =11A, V _{GS} =0V	-	2.0	-	μs
Reverse Recovery Charge	Q _{rr}	-di/dt=100A/μs, T _{ch} =25°C	-	20	-	μC

Thermal Characteristics

Description	Symbol	Test Conditions	min.	typ.	max.	Unit
Thermal resistance	R _{th(ch-c)}	Channel to case			0.4386	°C/W
	R _{th(ch-a)}	Channel to ambient			50.0	°C/W

Note *1 : T_{ch}≤150°C

Note *2 : Stating T_{ch}=25°C, I_{AS}=4.4A, L=76.9mH, V_{CC}=90V, R_G=10Ω
E_{AS} limited by maximum channel temperature and avalanche current.
See to 'Avalanche current' graph.

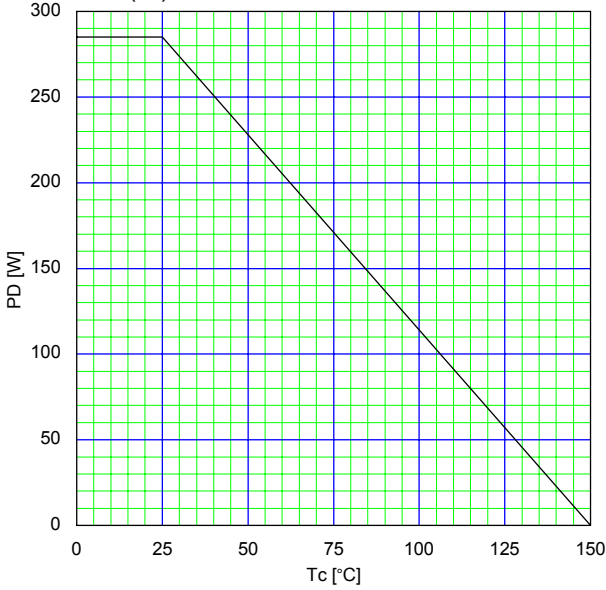
Note *3 : Repetitive rating : Pulse width limited by maximum channel temperature.

See to the 'Transient Thermal impedance' graph.

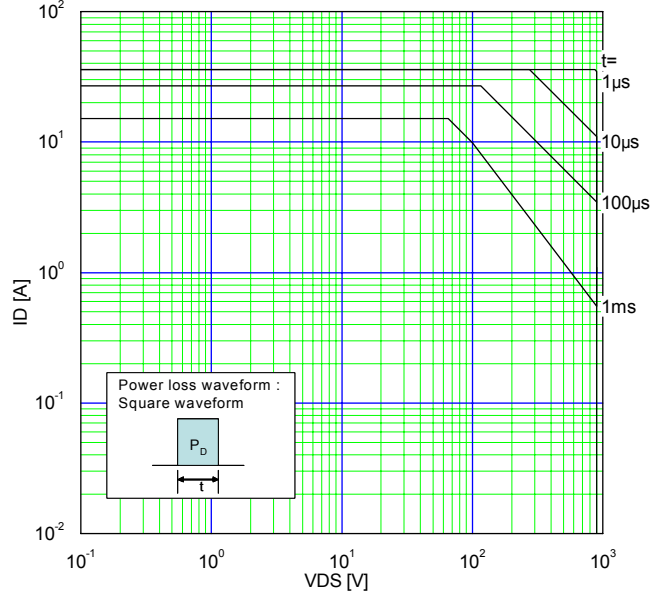
Note *4 : I_F≤I_D, -di/dt=100A/μs, V_{CC}≤BV_{DSS}, T_{ch}≤150°C.

Note *5 : I_F≤I_D, dv/dt=2.2kV/μs, V_{CC}≤BV_{DSS}, T_{ch}≤150°C.

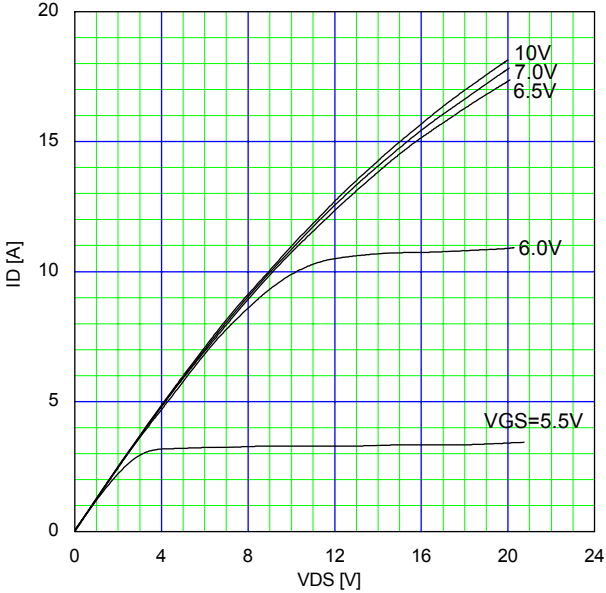
Allowable Power Dissipation
 $P_D = f(T_c)$



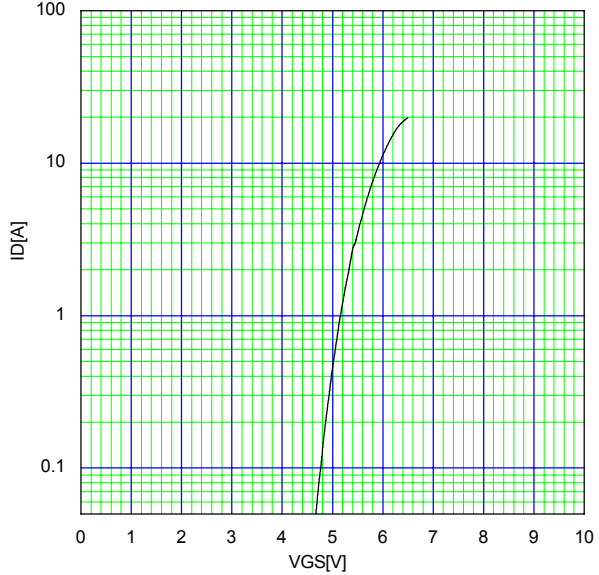
Safe Operating Area
 $I_D = f(V_{DS})$: Duty=0 (Single pulse), $T_c = 25^\circ\text{C}$



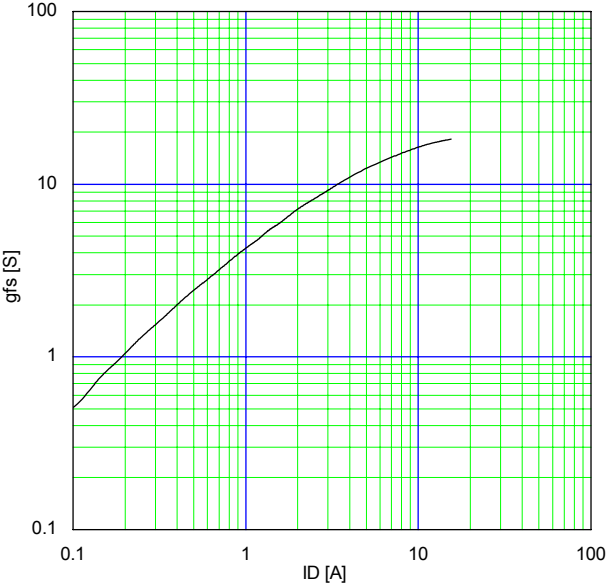
Typical Output Characteristics
 $I_D = f(V_{DS})$: 80 μs pulse test, $T_{ch} = 25^\circ\text{C}$



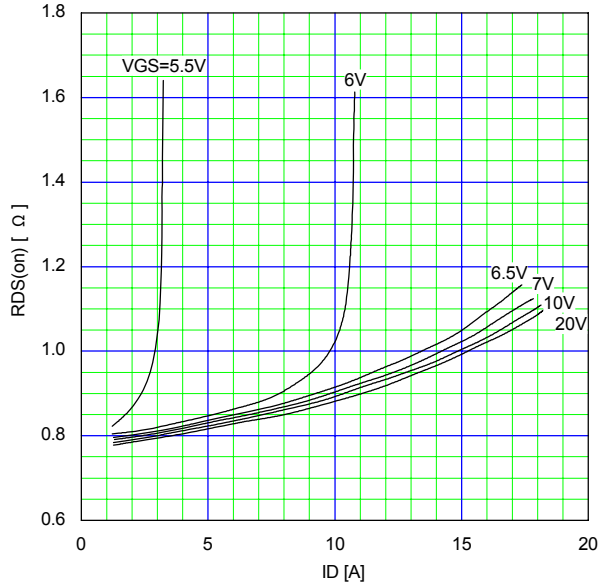
Typical Transfer Characteristic
 $I_D = f(V_{GS})$: 80 μs pulse test, $V_{DS} = 25\text{V}$, $T_{ch} = 25^\circ\text{C}$



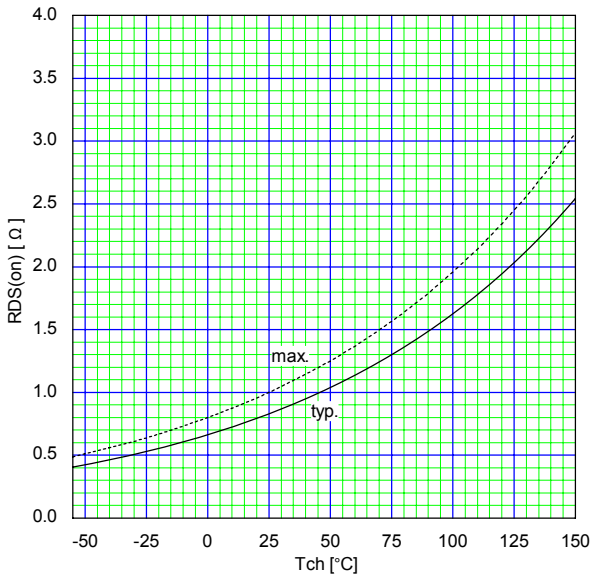
Typical Transconductance
 $g_{fs} = f(I_D)$: 80 μs pulse test, $V_{DS} = 25\text{V}$, $T_{ch} = 25^\circ\text{C}$



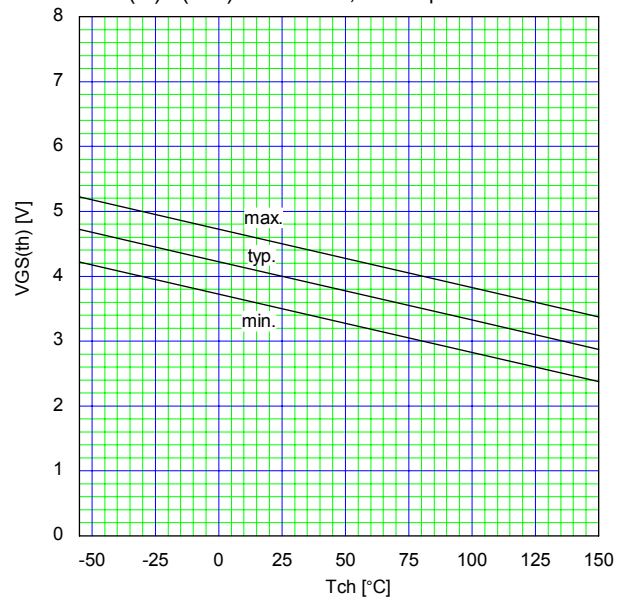
Typical Drain-Source on-state Resistance
 $R_{DS(on)} = f(I_D)$: 80 μs pulse test, $T_{ch} = 25^\circ\text{C}$



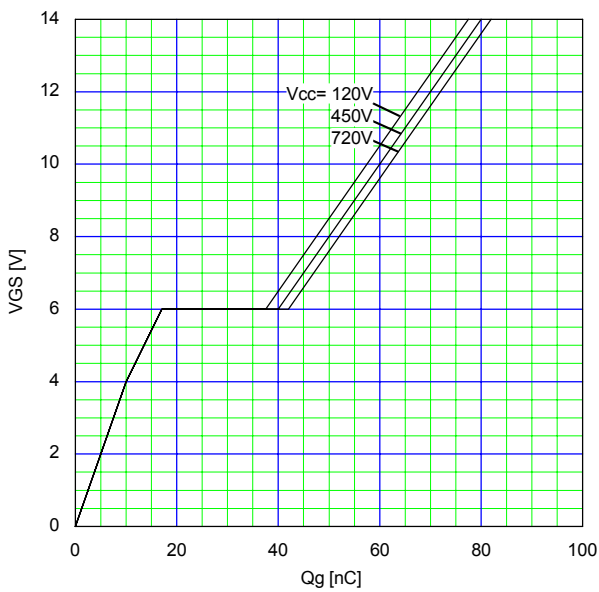
Drain-Source On-state Resistance
 $R_{DS(on)} = f(T_{ch})$; $I_D = 5.5A, V_{GS} = 10V$



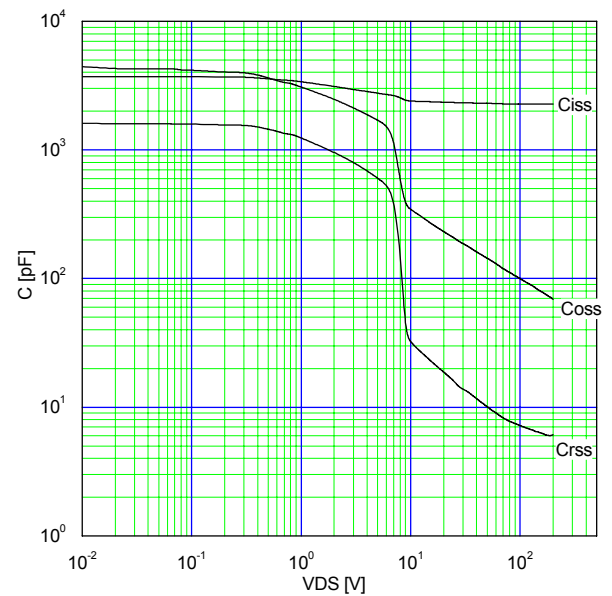
Gate Threshold Voltage vs. T_{ch}
 $V_{GS(th)} = f(T_{ch})$; $V_{DS} = V_{GS}, I_D = 250\mu A$



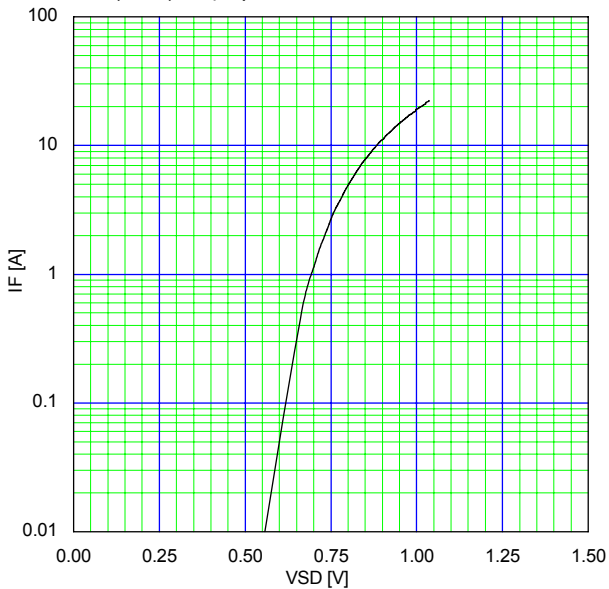
Typical Gate Charge Characteristics
 $V_{GS} = f(Q_g)$; $I_D = 11A, T_{ch} = 25^\circ C$



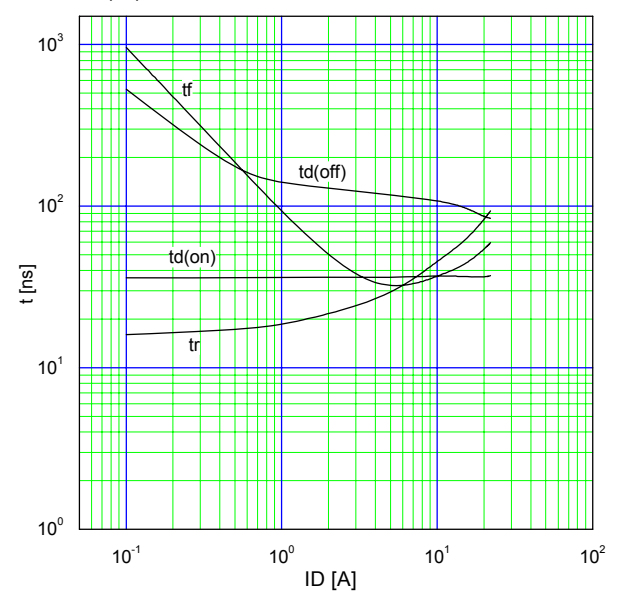
Typical Capacitance
 $C = f(V_{DS})$; $V_{GS} = 0V, f = 1MHz$



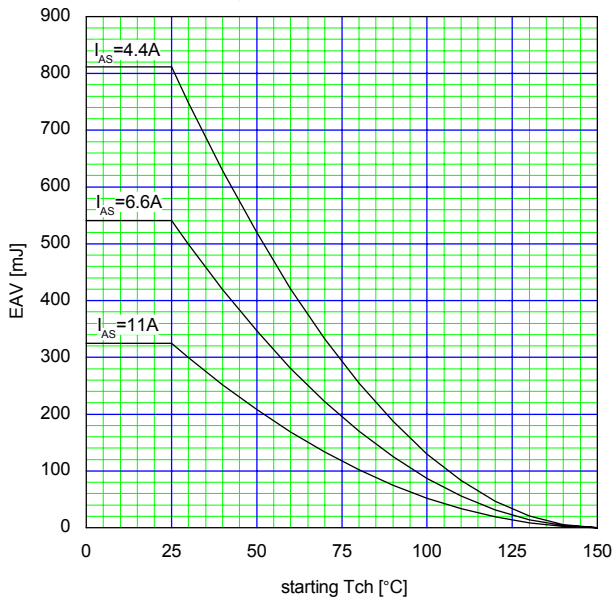
Typical Forward Characteristics of Reverse Diode
 $I_F = f(V_{SD})$; $80\mu s$ pulse test, $T_{ch} = 25^\circ C$



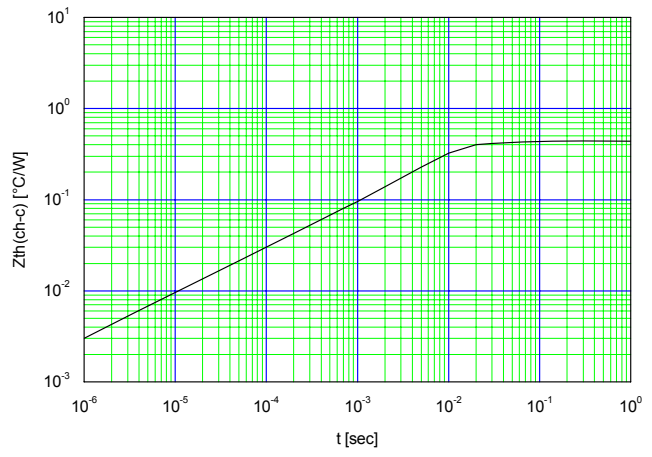
Typical Switching Characteristics vs. I_D
 $t = f(I_D)$; $V_{cc} = 600V, V_{GS} = 10V, R_G = 20\Omega$



Maximum Avalanche Energy vs. starting Tch
 $E(AV)=f(\text{starting Tch}):V_{CC}=90V, I(AV)\leq 11A$



Maximum Transient Thermal Impedance
 $Z_{th}(ch-c)=f(t):D=0$



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